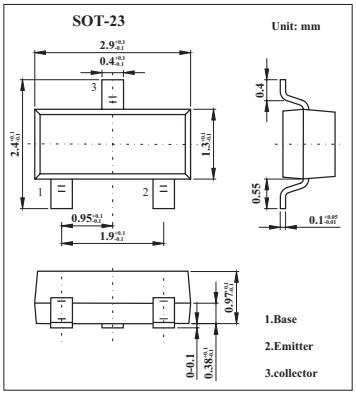
High Voltage Transistor

BSS63R



■ Features

- SOT23 PNP silicon planar

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-110	V
Collector-emitter voltage	V_{CEO}	-100	V
Emitter-base voltage	V_{EBO}	-6	V
Continuous collector current	I_C	-100	mA
Power dissipation	P_{tot}	330	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA	-110			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	I_C=-100μA	-100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA	-6			V
Collector-base cut-off current	I_{CBO}	V_{CB}=-90V V_{CB}=-90V,Ta = 150℃			-100 -50	nA μA
Emitter-base current	I_{EBO}	V_{EB}=-6V			-200	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-25mA, I_B=-2.5mA			-250	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-25mA, I_B=-2.5mA			-900	V
DC current gain	h_{FE}	I_C=-10mA,V_{CE}=-1V I_C=-25mA,V_{CE}=-1V	30 30			
Transitional frequency	f_T	I_C=25mA, V_{CE}=-5V, f=35MHz	50	85		MHz
Output capacitance	C_{obo}	V_{CB}=-10V, f=1MHz		3		pF

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

Marking	T6